

isc N-Channel MOSFET Transistor

STB11NM80

FEATURES

- Drain Current –I_D=11A@ T_C=25℃
- Drain Source Voltage-
 - : V_{DSS}= 800V(Min)
- · Static Drain-Source On-Resistance
 - : $R_{DS(on)} = 0.4 \Omega (Max) @ V_{GS} = 10V$
- 100% avalanche tested
- Minimum Lot-to-Lot variations for robust device performance and reliable operation



DESCRIPTION

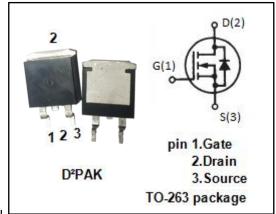
• Designed for use in switch mode power supplies and general purpose applications.

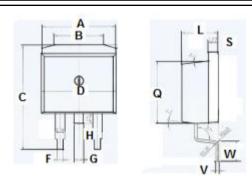
ABSOLUTE MAXIMUM RATINGS(Ta=25°C)

SYMBOL	PARAMETER	VALUE	UNIT
V _{DSS}	Drain-Source Voltage	800	V
V _{GS}	Gate-Source Voltage-Continuous	±30	V
I _D	Drain Current-Continuous	11	А
I _{DM}	Drain Current-Single Pluse	44	Α
P _D	Total Dissipation @T _C =25℃	150	W
TJ	Max. Operating Junction Temperature	-55~150	°C
T _{stg}	Storage Temperature	-55~150	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	MAX	UNIT
R _{th j-c}	Thermal Resistance, Junction to Case	0.83	°C/W





DIM	m	ım
DIIVI	MIN	MAX
Α	9.8	10.2
В	6.6	6.8
С	15.1	15.3
D	9.6	10
F	0.7	0.9
G	1.26	1.3
Н	1.2	1.45
L	4.4	4.6
Q	9.2	9.3
S	1.25	1.35
V	0.4	0.6
W	2.6	2.8

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ELECTRICAL CHARACTERISTICS

T_C=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT
V _{(BR)DSS}	Drain-Source Breakdown Voltage	ain-Source Breakdown Voltage V _{GS} = 0; I _D = 0.25mA			V
V _{GS(th)}	Gate Threshold Voltage	V_{DS} = V_{GS} ; I_D = 0.25mA	3	5	V
R _{DS(on)}	Drain-Source On-Resistance	V _{GS} = 10V; I _D = 5.5A		0.4	Ω
lgss	Gate-Body Leakage Current	V _{GS} = ±30V;V _{DS} = 0		±100	nA
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 800V; V _{GS} = 0		10	μА
V _{SD}	Forward On-Voltage	I _S = 11A; V _{GS} = 0		0.86	V

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